

NPN Silicon Epitaxial Planar Transistor

for use in driver stage of high voltage audio equipments.

The transistor is subdivided into three groups, M, L and K, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Collector 3. Base

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO}	60	V
Collector Emitter Voltage	V _{CEO}	60	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	300	mA
Base Current	I _B	60	mA
Power Dissipation	P _{tot}	600	mW
Junction Temperature	T _j	150	°C
Storage Temperature Range	Ts	-55 to +150	°C









Characteristics at T_{amb}=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V _{CE} =1V, I _C =50mA					
Current Gain Group M	h _{FE}	90	-	180	-
L	h _{FE}	135	-	270	-
К	h _{FE}	200	-	400	-
at V _{CE} =2V, I _C =300mA	h _{FE}	30	80	-	-
Base Emitter Voltage					
at I _C =10mA, V _{CE} =6V	V_{BE}	600	645	700	mV
Emitter Cutoff Current					
at V _{EB} =5V	I _{EBO}	-	-	100	nA
Collector Cutoff Current					
at V _{CB} =60V	I _{CBO}	-	-	100	nA
Collector Saturation Voltage					
at I _C =300mA, I _B =30mA	$V_{CE(sat)}$	-	0.15	0.6	V
Base Saturation Voltage					
at I _C =300mA, I _B =30mA	$V_{BE(sat)}$	-	0.86	1.2	V
Gain Bandwidth Product					
at V _{CE} =6V, I _E =-10mA	f _T	50	140	-	MHz
Collector to Base Capacitance					
at V _{CB} =6V, f=1MHz	C _{OB}		7.0	15	pF







